



# Flash Technology Update from Micron and Intel

## *3D NAND Technology Announcement*

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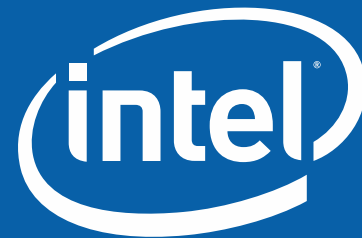
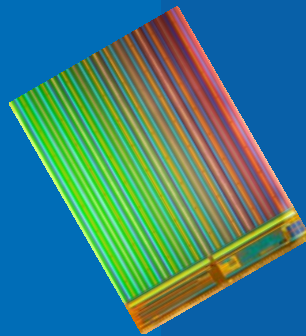
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# Micron and Intel – A Strong Partnership



# New 3D NAND Announcement Highlights

3x higher capacity  
than existing NAND technologies<sup>1</sup>

Enables >10TB  
in a standard 2.5" SSD

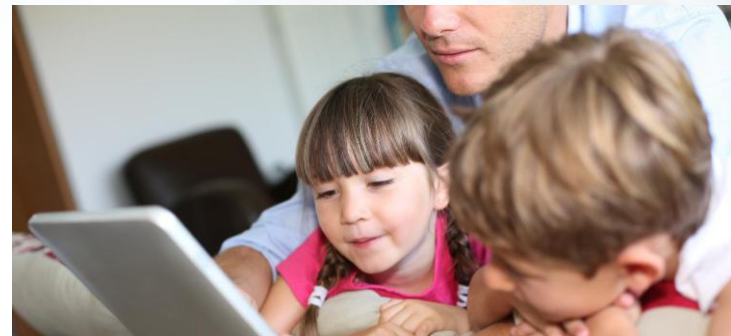
Extends Moore's  
Law for flash  
storage

1 Capacity difference based on comparison between Micron and Intel 384 Gb TLC 3D NAND die and other industry 3D NAND TLC



# Broad Range of Applications

Flash is pervasive and essential to a range of mobile consumer devices and data center deployments



# Ongoing Demand Growth



Mobility, performance and power requirements  
continue to drive flash demand

Source: Industry analysts

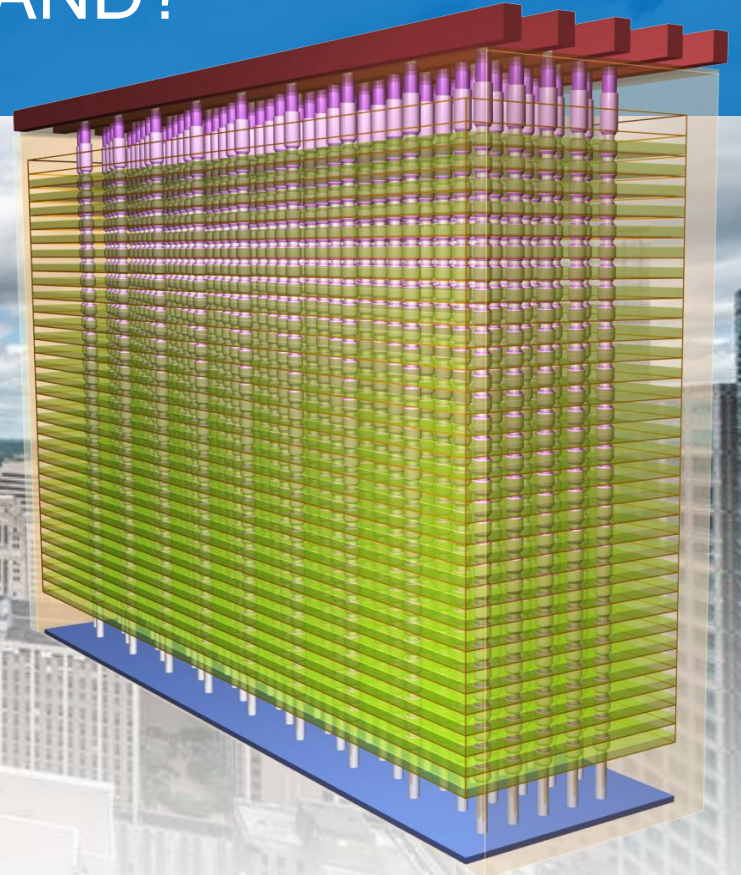
# What is 3D NAND?

3D NAND cells are built vertically – like a skyscraper



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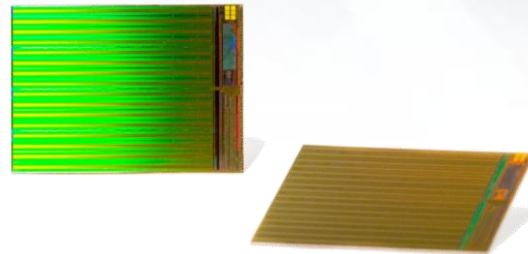


# A Disruptive Storage Architecture

CAPACITY	Enables the highest-density flash device ever developed
COST	Architected to achieve better cost efficiency than 2D NAND
CONFIDENCE	3D architecture increases performance and endurance

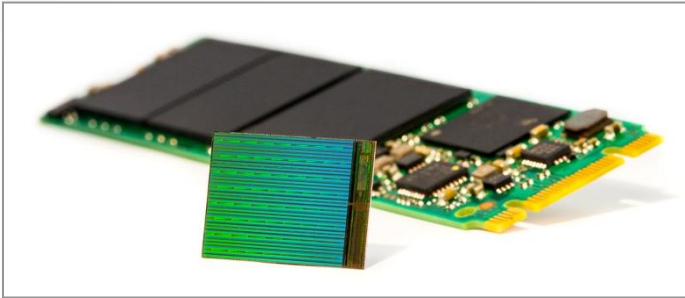
**256 Gb**  
MLC

**384 Gb**  
TLC



# Industry benefits – Market Impact

3D NAND Flash will serve the most demanding markets



Meeting the capacity demand

With 3D NAND, an M.2 drive could hold more than 3.5TB

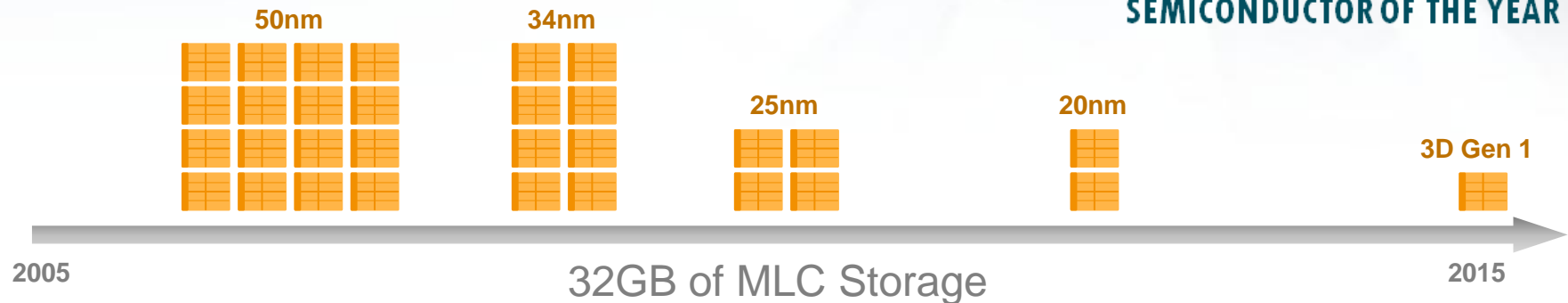


# Award-Winning Flash Leadership

A decade of flash R&D collaboration

Multiple industry awards

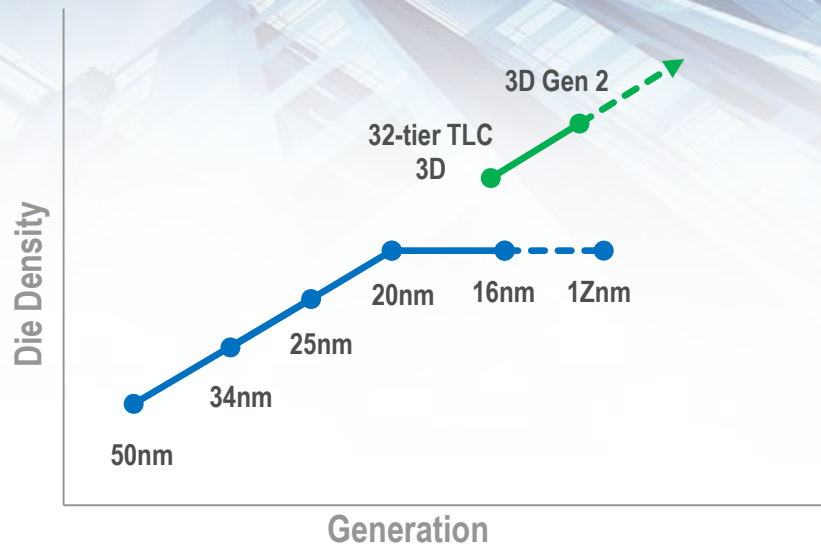
Dramatic impact on solid-state storage





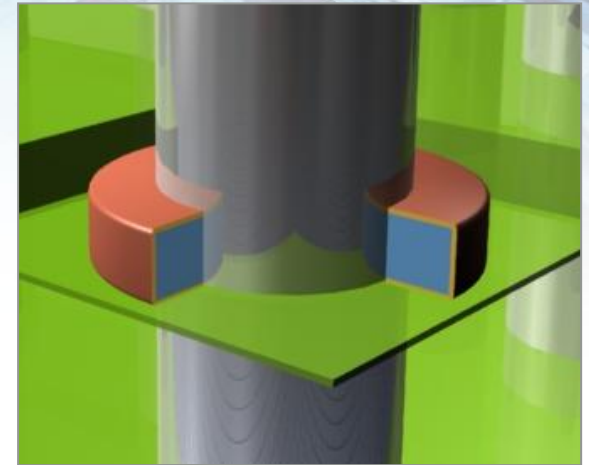
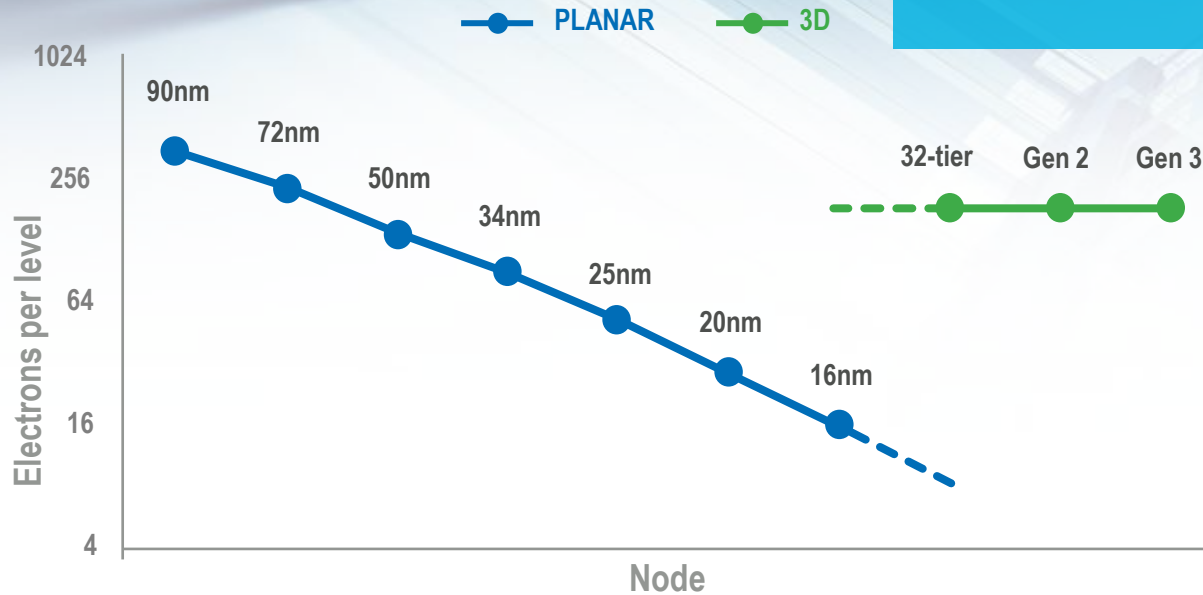
# Why is 3D Necessary?

3D NAND extends the Moore's Law path for flash storage



# Performance and Reliability

Cell design improves performance and reliability



# Floating Gate: A Proven Cell Structure

First floating gate cell in 3D NAND

The cell structure of choice in the vast majority of flash

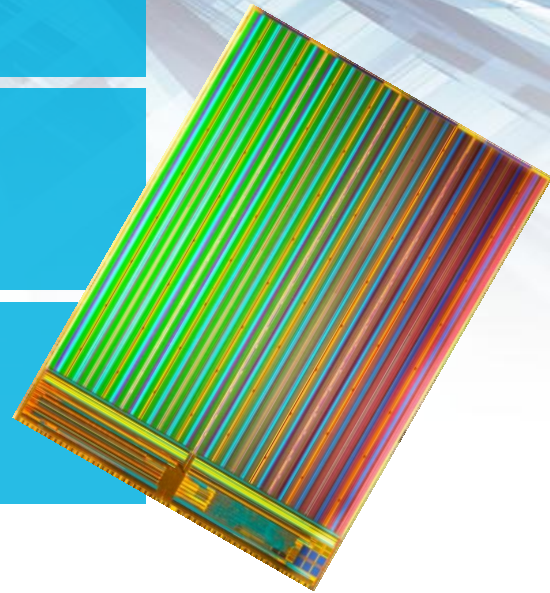
Proven foundation limits variables, increases quality and reliability

# Summary

3x higher capacity than existing NAND technologies

Enables >10TB in a standard 2.5" SSD

Extends Moore's Law for flash storage





# Q&A

